

-150V P-Channel Enhancement Mode MOSFET

Features

- Advanced HEFET™ Technology
- Ultra Low On-Resistance
- Excellent $Q_g \times R_{DS(on)}$ Product
- 100% avalanche tested
- 175°C Operating Temperature
- Lead Free and Green Devices Available (RoHS Comp)

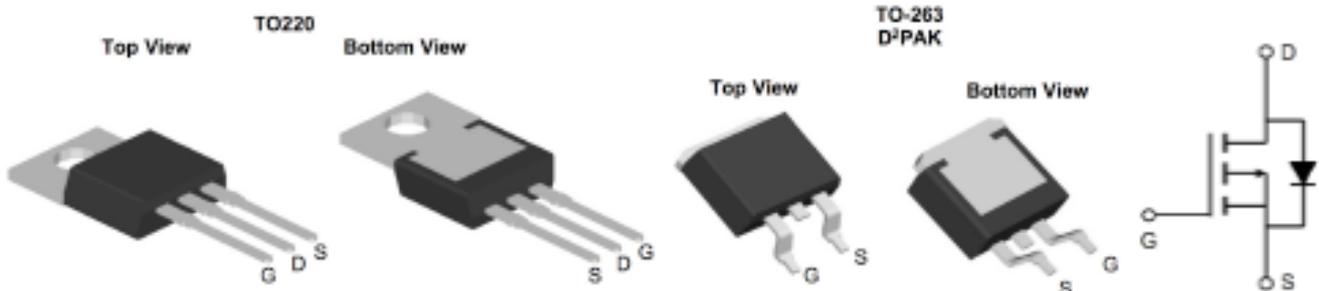
Applications

- Motor Drives
- Uninterruptible Power Supplies
- DC/DC converter
- General Purpose Applications



$V_{DS} = -150V$ $I_D = -45A$

$R_{DS(ON)} < 80m\Omega$ @ $V_{GS}=10V$



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
XPX45P15TU	TO-220-3L	XPX45P15TU XXX YYYY	1000
XPX45P15TU	TO-263-3L	XPX45P15TU XXX YYYY	800

Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-150	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-45	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $-V_{GS}$ @ $-10V^1$	-27.2	A
IDM	Pulsed Drain Current ²	-120	A
EAS	Single Pulse Avalanche Energy ³	402	mJ
IAS	Avalanche Current	48	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	65.8	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62.5	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	1.5	$^\circ C/W$

Electrical Characteristics (T_J =25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
BVDSS	Drain to Source Breakdown Voltage	I _D =-250 A, V _{GS} =0V	-150	-175	-	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =-120 V, V _{GS} =0V	-	-	-1	nA
IGSS	Gate to Source Leakage Current	V _{GS} =±25 V, V _{DS} =0V	-	-	±100	nA
VGS(th)	Gate to Source Threshold Voltage	V _{GS} =V _{DS} , I _D =-250A	-1.2	-2.0	-3.0	V
RDS(on)	Static Drain to Source On Resistance	V _{GS} =-10V, I _D =-3 A	-	80	107	mΩ
RDS(on)	Static Drain to Source On Resistance	V _{GS} =-4.5V, I _D =-2.7 A	-	90	137	mΩ
GFS	Forward Transconductance	V _{DS} =-10V, I _D =-3 A	-	12	-	S
Ciss	Input Capacitance	V _{DS} =-75V, V _{GS} =0V, f=1MHz	-	1535	2045	pF
Coss	Output Capacitance		-	125	170	pF
Crss	Reverse Transfer Capacitance		-	6	10	pF
Rg	Gate Resistance		0.1	1.4	3	Ω
td(on)	Turn-On Delay Time	V _{DD} =-75V, I _D =-3A, V _{GS} =-10V, R _{GEN} = 6	-	12	23	ns
tr	Rise Time		-	3.3	10	ns
td(off)	Turn-Off Delay Time		-	22	36	ns
tf	Fall Time		-	9.6	20	ns
VSD	Source to Drain Diode Forward Voltage	V _{GS} = 0 V, I _S = -3 A (Note 2)	-	-0.80	-1.3	V
trr	Reverse Recovery Time	I _F = -3 A, di/dt = 100 A/s	-	77	123	ns

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3、 The EAS data shows Max. rating . The test condition is VDD =-120V,VGS =-10V,L=0.1mH,IAS =-48A
- 4、 The power dissipation is limited by 150°C junction temperature
- 5、 The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

Typical Characteristics

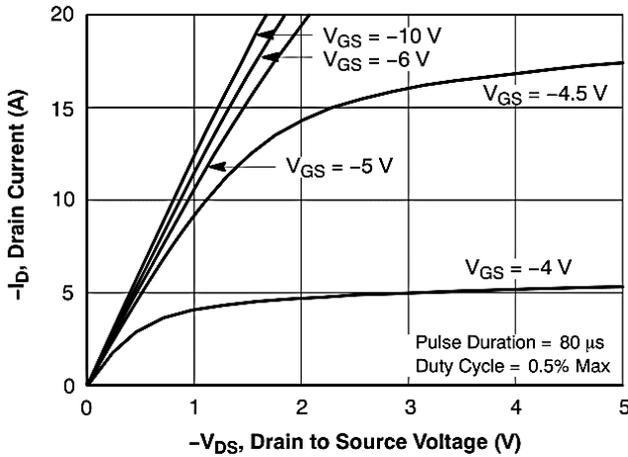


Figure 1. On Region Characteristics

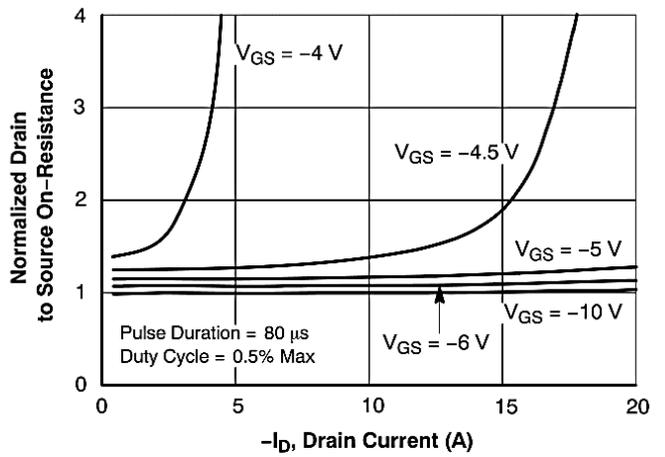


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

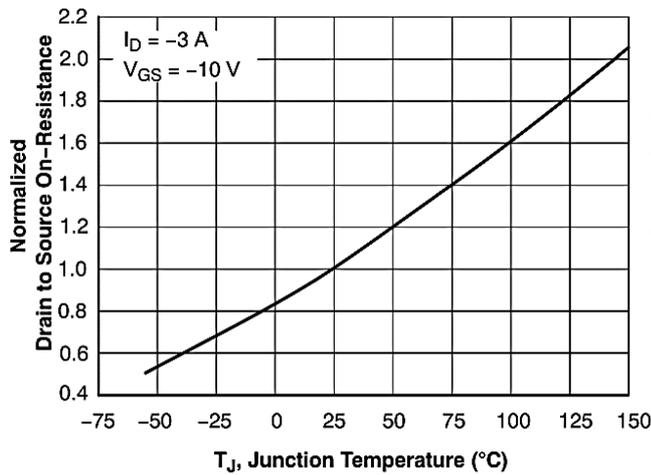


Figure 3. Normalized On Resistance vs. Junction Temperature

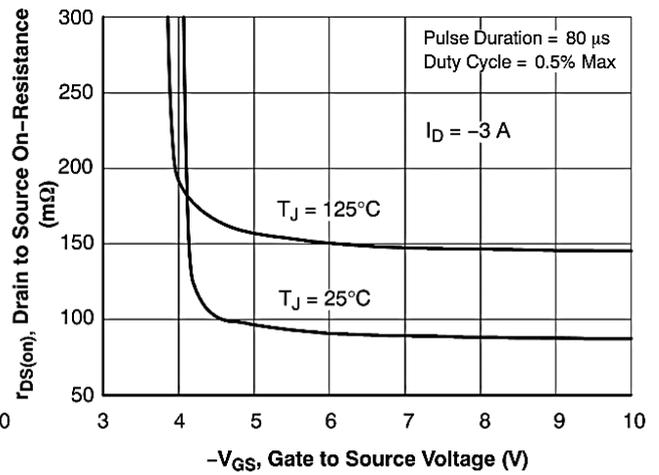


Figure 4. On-Resistance vs. Gate to Source Voltage

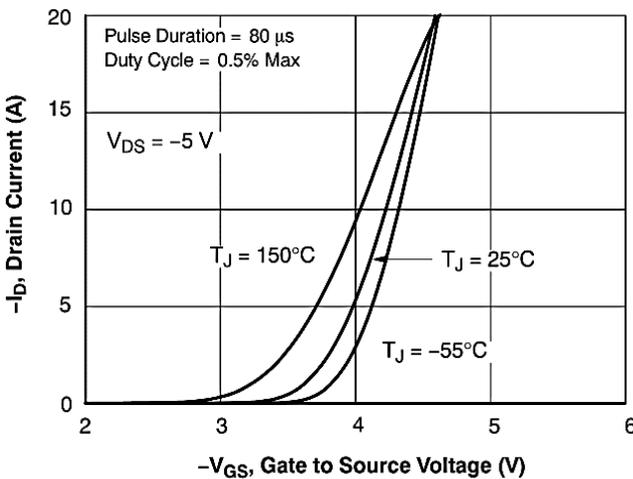


Figure 5. Transfer Characteristics

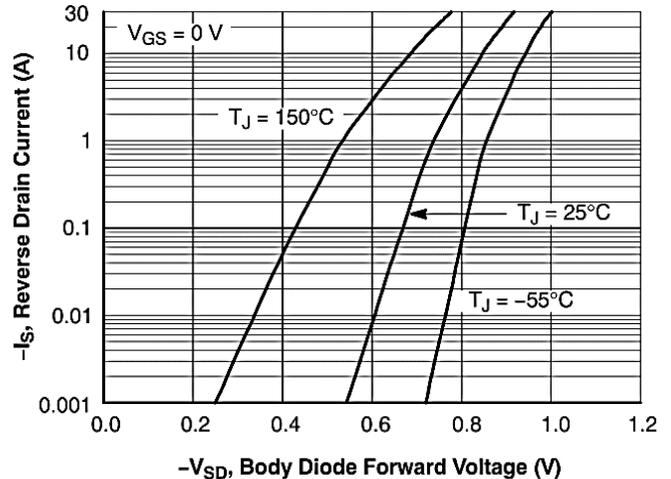


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

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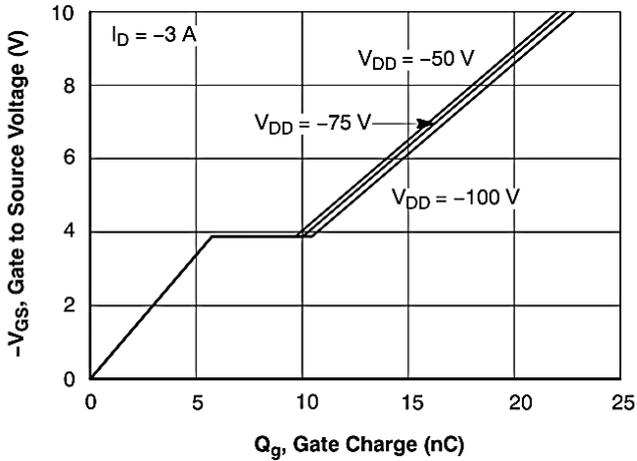


Figure 7. Gate Charge Characteristics

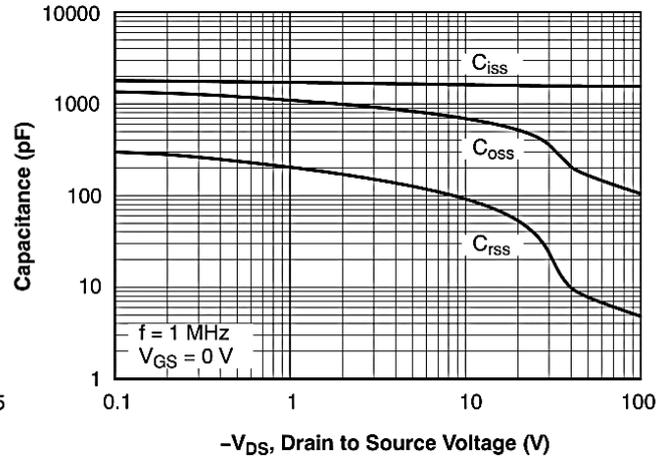


Figure 8. Capacitance vs. Drain to Source Voltage

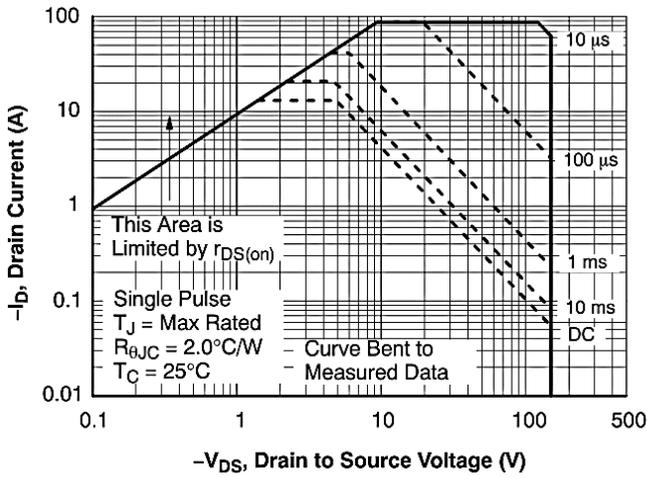


Figure 9. Forward Bias Safe Operating Area

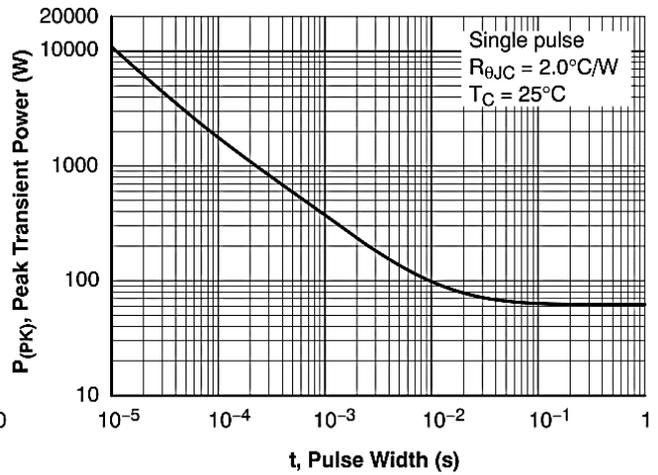


Figure 10. Single Pulse Maximum Power Dissipation

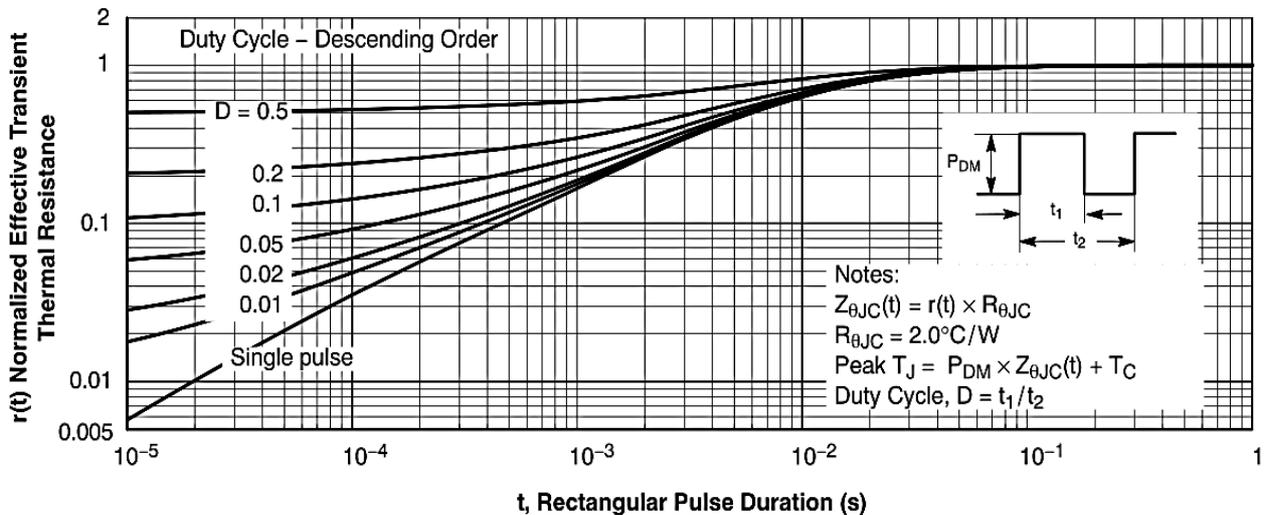
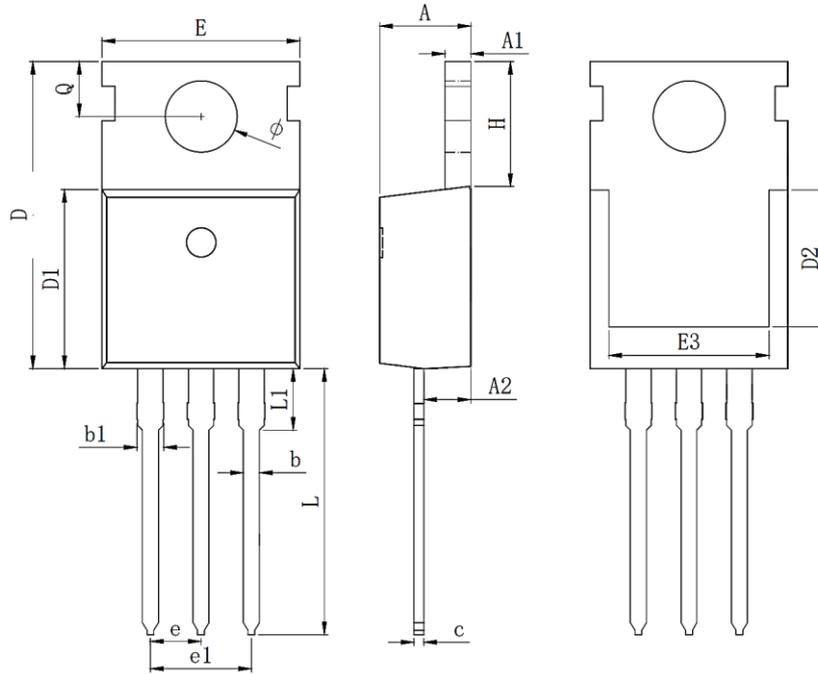
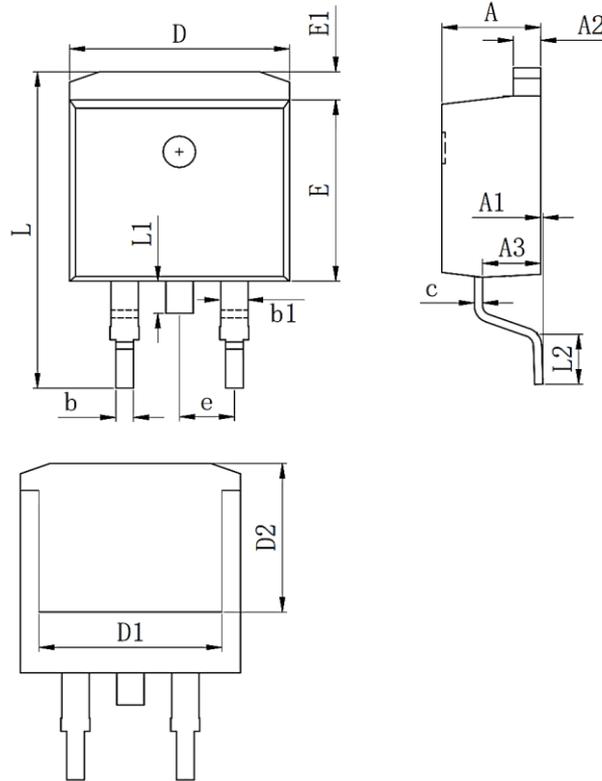


Figure 11. Junction-to-Case Transient Thermal Response Curve

Package Mechanical Data-TO-220C-3L


Symbol	Dim in mm		
	min	tpy	max
A	4.25	4.5	4.7
A1	1.15	1.3	1.45
A2	2.15	2.35	2.55
b	0.65	0.8	0.95
b1	1.15	1.35	1.55
c	0.35	0.5	0.65
D	14.3	15.3	16.3
D1	8.8	9.1	9.4
D2	6.3REF		
E	9.7	10	10.3
E3	7	8	9
e	2.54BSC		
e1	5.08BSC		
L	12.7	13.5	13.9
L1		3.1	3.4
H	6	6.5	6.85
Q	2.6	2.8	3
φ	3.4	3.6	3.8

Package Mechanical Data-TO-263C-3L


Symbol	Dim in mm		
	min	tpy	max
A	4.37	4.57	4.77
A1	0		0.25
A2	1.22	1.27	1.42
A3	2.49	2.69	2.89
b	0.7	0.81	0.96
b1	1.17	1.27	1.47
c	0.3	0.38	0.53
D	9.86	10.16	10.36
D1	8.4REF		
D2	7.073REF		
E	8.5	8.7	8.9
E1	1.07	1.27	1.47
e	2.54BSC		
L	17.7	15.1	15.5
L1	1.4	1.55	1.7
L2	2	2.3	2.6
H	6	6.5	6.85
Q	2.6	2.8	3
φ	3.4	3.6	3.8

Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time
Pb device	245°C ±5°C	5sec ±1sec
Pb-Free device	260°C +0/-5°C	5sec ±1sec



This integrated circuit can be damaged by ESD. UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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